

**In the Claims:**

**Marked up version of once amended claim 33:**

33. (Once Amended) A composite structure in an IC chip, said composite structure comprising:

- a first metal pad structure comprising a first interconnect metal;
- a first via pad structure below said first metal pad structure, said first via pad structure comprising a plurality of segments of a first via metal and a first plurality of dielectric fillers, at least one of said plurality of segments of said first via metal contacting said first interconnect metal.

**Clean version of once amended claim 33:**

*Sub C1*

33. (Once Amended) A composite structure in an IC chip, said composite structure comprising:

- a first metal pad structure comprising a first interconnect metal;
- a first via pad structure below said first metal pad structure, said first via pad structure comprising a plurality of segments of a first via metal and a first plurality of dielectric fillers, at least one of said plurality of segments of said first via metal contacting said first interconnect metal.

*DK*

**Marked up version of once amended claim 45:**

45. (Once Amended) A method for fabricating a composite structure in an IC chip, said method comprising steps of:

fabricating a first via pad structure, said first via pad structure comprising a plurality of segments of a first via metal and a first plurality of dielectric fillers;

fabricating a first metal pad structure above said first via pad structure, said first metal pad structure comprising a first interconnect metal, said first interconnect metal contacting at least one of said plurality of segments of said first via metal.

**Clean version of once amended claim 45:**

45. (Once Amended) A method for fabricating a composite structure in an IC chip, said method comprising steps of:

fabricating a first via pad structure, said first via pad structure comprising a plurality of segments of a first via metal and a first plurality of dielectric fillers;

fabricating a first metal pad structure above said first via pad structure, said first metal pad structure comprising a first interconnect metal, said first interconnect metal contacting at least one of said plurality of segments of said first via metal.

**Marked up version of once amended claim 51:**

51. (Once Amended) A composite structure in an IC chip, said composite structure comprising:

a first via pad structure comprising a first via metal;  
a first metal pad structure below said first via pad structure, said first metal pad structure comprising a plurality of segments of a first interconnect metal and a first plurality of dielectric fillers, at least one of said plurality of segments of said first interconnect metal contacting said first via metal.

**Clean version of once amended claim 51:**

*SIC 3*  
51. (Once Amended) A composite structure in an IC chip, said composite structure comprising:  
a first via pad structure comprising a first via metal;  
a first metal pad structure below said first via pad structure, said first metal pad structure comprising a plurality of segments of a first interconnect metal and a first plurality of dielectric fillers, at least one of said plurality of segments of said first interconnect metal contacting said first via metal.

*BB*

**Marked up version of once amended claim 62:**

62. (Once Amended) A composite structure in an IC chip, said composite structure comprising a plurality of segments of a first interconnect metal and a first plurality of dielectric fillers, said plurality of segments of said first interconnect metal being electrically connected to each other.

**Clean version of once amended claim 62:**

B4 62. (Once Amended) A composite structure in an IC chip, said composite structure comprising a plurality of segments of a first interconnect metal and a first plurality of dielectric fillers, said plurality of segments of said first interconnect metal being electrically connected to each other.

**Please add the following new claims:**

Sub C4  
--69. A composite structure comprising:

a first via pad structure comprising a first via metal;

a first metal pad structure below said first via pad structure, said first metal pad structure comprising a plurality of segments of a first interconnect metal and a first plurality of dielectric fillers, at least one of said plurality of segments of said first interconnect metal contacting said first via metal;

B5 a second via pad structure below said first metal pad structure, said second via pad structure comprising a plurality of segments of a second via metal and a second plurality of dielectric fillers, at least one of said plurality of segments of said second via metal contacting said first interconnect metal.--

--70. The composite structure of claim 69 wherein said second via metal is selected from the group consisting of copper and tungsten.--

--71. The composite structure of claim 69 wherein said second plurality of dielectric fillers comprise a low-k dielectric.--

cont  
B5  
--72. The composite structure of claim 71 wherein said low-k dielectric is selected from the group consisting of porous silica, fluorinated amorphous carbon, fluoropolymer, parylene, polyarylene ether, silsesquioxane, fluorinated silicon dioxide, and diamondlike carbon.--

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